

# High Performance InGaAs p-i-n Photodiode

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## 13PD150-ST, -SMA, -FC, -SC

The 13PD150-ST, an InGaAs photodiode with a 150 $\mu$ m-diameter photosensitive region packaged in a TO-46 header and aligned in an AT&T ST active device mount, is intended for high coupling efficiency to multi-mode fiber in moderate-to-high speed applications. Planar semiconductor design and dielectric passivation provide superior low noise performance. Reliability is assured by hermetic sealing and 100% purge burn-in (200°C, 15 hours, Vr = 20V). The ST receptacle is suitable for bulkhead and PC board mounting.



### Features:

- Planar Structure
- Dielectric Passivation
- 100% Purge Burn-in
- High Responsivity

### DEVICE CHARACTERISTICS

Parameters	Test Conditions	Minimum	Typical	Maximum	Units
Operating Voltage				-20	Volts
Dark Current	-5V		0.5	2.5	nA
Capacitance	-5V		0.7	2.25	pF
Responsivity	1300nm	0.7	0.8		A/W
Rise/Fall				0.5	ns

### ABSOLUTE MAXIMUM RATINGS

Reverse Voltage	20 Volts
Forward Current	5mA
Reverse Current	1mA
Operating Temperature	-40°C to +85°C
Storage Temperature	-40°C to +85°C
Soldering Temperature	250°C

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